ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE6248
Silicon Schottky Barrier Rectifier

Features:

- Guarding for Stress Protection
- Low Forward Voltage
- High Current Capability
- High Surge Capability

Maximum Ratings and Electrical Characteristics:

(T_A = +25°C unless otherwise specified. Resistive or inductive load.)

Maximum Recurrent Peak Reverse Voltage, V_{RRM} 600V

Maximum RMS Voltage, V_{RMS} 420V

Maximum DC Blocking Voltage, V_{DC} 600V

Maximum Average Rectified Forward Current (T_C = +100°C), $I_{F(AV)}$ 16A

Peak Forward Surge Current, I_{FSM}

(8.3ms single half sine–wave superimposed on rated load) 250A

Maximum Instantaneous Forward Voltage (I_F = 16A), V_F 1.5V

Maximum DC Reverse Current (rated DC Blocking Voltage), I_R

T_C = +25°C 10µA

T_C = +100°C 500µA

Maximum Reverse Recovery Time (T_J = +25°C, Note 1), T_{RR} 50ns

Typical Junction Capacitance (Note 2), C_J 145pF

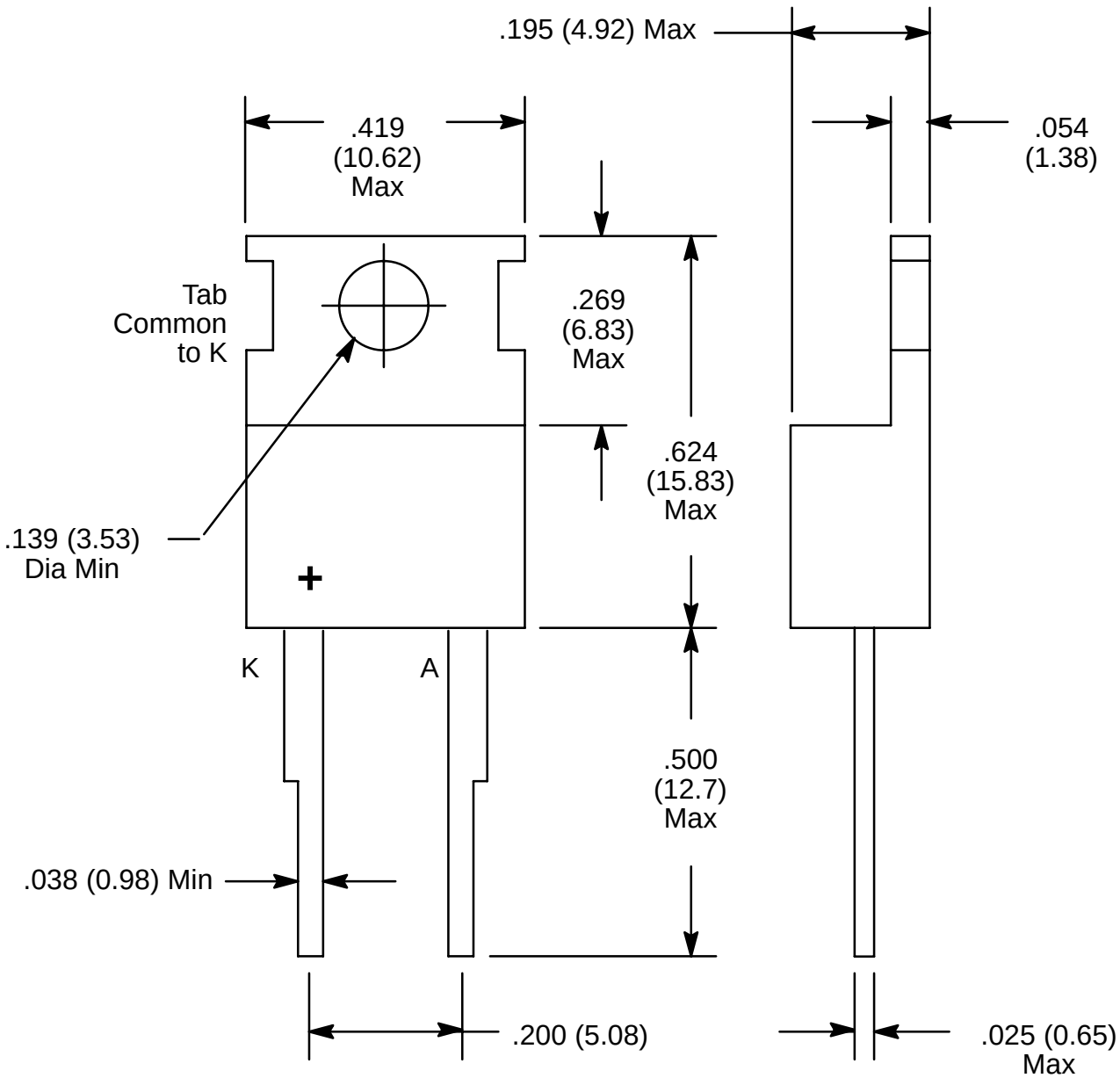
Typical Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 1.5°C/W

Operating Junction Temperature Range, T_J . . . . . –55° to +175°C

Storage Temperature Range, T_{stg} . . . . . –55° to +175°C

Note 1. Reverse Recovery Test Conditions: I_F = 500mA, I_R = 1A, recover to 250mA.

Note 2. Measured at 1MHz and applied reverse voltage of 4V.


.195 (4.92) Max
.419
(10.62)
Max
.054
(1.38)
Tab
Common
to K
.269
(6.83)
Max
.624
(15.83)
Max
.139 (3.53)
Dia Min
K
A
.500
(12.7)
Max
.038 (0.98) Min
.200 (5.08)
.025 (0.65)
Max